	Application No.	Applicant(s)	
	10/792,121	CHEN, CHUNG ZEN	1
Notice of Allowability	Examiner	Art Unit	
	Pho M. Luu	2824	
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.31	S (OR REMAINS) CLOSED in (i) or other appropriate commur RIGHTS. This application is su	this application. If not included nication will be mailed in due co	d ourse. THIS
1. This communication is responsive to			
2. The allowed claim(s) is/are <u>1-25</u> .			
3. ☐ Acknowledgment is made of a claim for foreign priority ua) ☐ All b) ☐ Some* c) ☐ None of the:	inder 35 U.S.C. § 119(a)-(d) or	· (f).	
 Certified copies of the priority documents hav 	e been received.		
Certified copies of the priority documents hav	e been received in Application	No	
Copies of the certified copies of the priority do	ocuments have been received	in this national stage application	on from the
International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received:			
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDON! THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		a reply complying with the requ	uirements
4. A SUBSTITUTE OATH OR DECLARATION must be subn INFORMAL PATENT APPLICATION (PTO-152) which give			TICE OF
5. X CORRECTED DRAWINGS (as "replacement sheets") mu	st be submitted.		
(a) ☐ including changes required by the Notice of Draftsper	son's Patent Drawing Review	(PTO-948) attached	
1) ☐ hereto or 2) ☐ to Paper No./Mail Date	_ •		
(b) ☐ including changes required by the attached Examiner Paper No./Mail Date 11/22/05.	's Amendment / Comment or i	n the Office action of	
Identifying indicia such as the application number (see 37 CFR areach sheet. Replacement sheet(s) should be labeled as such in			ack) of
6. DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT	osit of BIOLOGICAL MATE FOR THE DEPOSIT OF BIOL	RIAL must be submitted. No LOGICAL MATERIAL.	ote the
Attachment(s) 1. ☑ Notice of References Cited (PTO-892)	E □ Notice of Info	rmal Datast Application (DTO)	152)
 Notice of References Cited (PTO-692) DNotice of Draftperson's Patent Drawing Review (PTO-948): 		rmal Patent Application (PTO-	102)
	Paper No./N	lail Date mendment/Comment	
 Information Disclosure Statements (PTO-1449 or PTO/SB/ Paper No./Mail Date 03/03/04 	08), 7. ☐ Examiner's A	mendment/Comment	
Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. 🛛 Examiner's S	tatement of Reasons for Allow	/ance
	9. ⊠ Other <u>Search</u>	History.	

DETAILED ACTION

1. Claims 1-25 are pending in the application.

Information Disclosure Statement

Acknowledgment is made of applicant's Information Disclosure Statement
 (IDS) Form PTO-1449, filed 03 March 2004. The information disclosed
 therein was considered.

Drawings

3. Figures 2 should be designated by a legend such as --Prior Art-- because only that which is old is illustrated. See MPEP § 608.02(g). A proposed drawing correction or corrected drawings are required in reply to the Office action to avoid abandonment of the application. The objection to the drawings will not be held in abeyance.

Allowance

4. Claims 1-25 is allowance.

The following is an examiner's statement of reasons for allowance:

There is no teaching or suggestion in the prior art to: "detecting during the selected time period whether the bit line exhibits leakage current above the threshold value in a step of the method of overerase correction for memory cell in a memory array after the memory cell have been erased" as claimed in the independent claim 1, independent claim 19 and independent claim 25; or

Application/Control Number: 10/792,121

Art Unit: 2824

"detecting during the selected time period whether the bit line exhibits leakage current above the threshold value in a semiconductor device circuitry for overerase correction of the memory cell after the memory cell have been erased" as claimed in the independent claim 8; or

"an overerase verify circuit detecting whether a selected bit line exhibits leakage current above a threshold voltage during the selected time period of a semiconductor device circuitry for overerase correction of the memory cell after the memory cell have been erased" as claimed in the independent claim 24.

5. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Lee et al. (US. 5,822,252) disclosed a flash memory and decoder with over-erase repair that can provide three word-line voltage to overcome the over-erased problems.

Tang et al. (US. 6,023,426) disclosed a method of correcting over-erased memory cell in a flash EEPROM memory cell after erase so as to produce a narrow threshold voltage.

Application/Control Number: 10/792,121 Page 4

Art Unit: 2824

7. Any inquiry concerning this communication or earlier communications from the

Examiner should be directed to Pho M. Luu whose telephone number is

571.272.1876. The examiner can normally be reached on M-F 8:00AM – 5:00PM.

If attempts to reach the Examiner by telephone are unsuccessful, the Examiner's

Supervisor, Richard Elms, can be reached on 571.272.1869. The official fax number for

the organization where this application or proceeding is assigned is 703.872.9306 for all

official communications.

Information regarding the status of an application may be obtained from the

Patent Application Information Retrieval (PAIR) system. Status information for

published applications may be obtained from either Private PAIR or Public PAIR.

Status information for unpublished applications is available through Private PAIR only.

For more information about the PAIR system, see

http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

PML

22 November 2005

van thu nguyên Pimary Examiner